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## N-Channel 30 V (D-S) MOSFET

# PowerPAK® 1212-8SH

Top View

**Bottom View** 

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	30				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0060				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.0080				
Q <sub>g</sub> typ. (nC)	12				
I <sub>D</sub> (A) <sup>a, g</sup>	35				
Configuration	Single				

#### **FEATURES**

- TrenchFET® power MOSFET
- 100 % R<sub>g</sub> and UIS tested

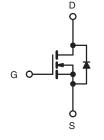




COMPLIANT HALOGEN **FREE** 

#### **APPLICATIONS**

- DC/DC converter
  - Notebook
  - POL



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH402DN-T1-GE3

DADAMETED	-	0)/14001			
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	30	V	
Gate-source voltage		$V_{GS}$	± 20	v	
	T <sub>C</sub> = 25 °C		35 <sup>a, g</sup>		
Continuous drain surrent (T. 150 °C)	T <sub>C</sub> = 70 °C		35 <sup>g</sup>		
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	19 <sup>b, c</sup>	A	
	T <sub>A</sub> = 70 °C		15 <sup>b, c</sup>	A	
Pulsed drain current		I <sub>DM</sub>	70		
Avalanche current	1 0111	I <sub>AS</sub>	35		
Avalanche energy	L = 0.1 mH	E <sub>AS</sub>	61	mJ	
Continuous source durin diada surrent	T <sub>C</sub> = 25 °C	1	43	A	
Continuous source-drain diode current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	3.2 b, c	A	
Maximum power dissipation	T <sub>C</sub> = 25 °C		52		
	T <sub>C</sub> = 70 °C	D	33	14/	
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.8 b, c	W	
	T <sub>A</sub> = 70 °C		2 b, c		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	0.0	
Soldering recommendations (peak temperature) d, e		ŭ	260	°C	

THERMAL RESISTANCE RATING	<b>as</b>				
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient b, f	t ≤ 10 s	$R_{thJA}$	24	33	°C/W
Maximum junction-to-case (drain)	Steady state	$R_{thJC}$	1.9	2.4	C/VV

- a. Based on T<sub>C</sub> = 25 °C
- Surface mounted on 1" x 1" FR4 board
- d. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
  e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
  f. Maximum under steady state conditions is 81 °C/W

- Package limited



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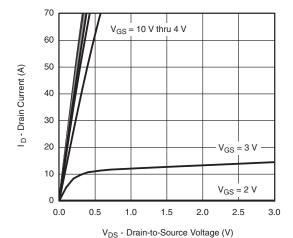
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static			•	•		
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	J 050 A	-	24	-	\//00
V <sub>GS(th)</sub> temperature coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = 250 μA	-	-6	-	mV/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_{D} = 250 \mu A$	1.15	-	2.2	٧
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zana anta malta an aluain annuant		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	5	μA
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	50	-	-	Α
Drain course on state registance 3	Б	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 19 A	-	0.0048	0.0060	0
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 16.6 A	-	0.0064	0.0080	Ω
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 19 A	-	82	-	S
Dynamic <sup>b</sup>				•		
Input capacitance	C <sub>iss</sub>		-	1700	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	350	-	pF
Reverse transfer capacitance	C <sub>rss</sub>		-	140	-	
Total gata abarga	0	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 19 \text{ A}$				
Total gate charge	$Q_g$		-	12	21	nC
Gate-source charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 19 \text{ A}$	-	5.4	-	110
Gate-drain charge	$Q_{gd}$		-	4.6	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz	-	1.2	2.4	Ω
Turn-on delay time	t <sub>d(on)</sub>		-	25	40	
Rise time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 1.5 $\Omega$	-	20	30	
Turn-off delay time	t <sub>d(off)</sub>	$I_D\cong 10$ A, $V_{GEN}=4.5$ V, $R_g=1~\Omega$	-	25	40	
Fall time	t <sub>f</sub>		-	15	25	20
Turn-on delay time	t <sub>d(on)</sub>		-	12	20	ns -
Rise time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 1.5 $\Omega$	-	10	15	
Turn-off delay time	t <sub>d(off)</sub>	$I_D \cong 10$ A, $V_{GEN} = 10$ V, $R_g = 1$ $\Omega$	-	25	40	
Fall time	t <sub>f</sub>		-	10	15	
Drain-Source Body Diode Characteristi	cs					
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	30	۸
Pulse diode forward current	I <sub>SM</sub>		-	-	70	Α
Body diode voltage	$V_{SD}$	I <sub>S</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.8	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>		-	25	50	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/µs},$	-	17	35	nC
Reverse recovery fall time	t <sub>a</sub>	T <sub>J</sub> = 25 °C	-	13	-	
Reverse recovery rise time	t <sub>b</sub>		_	12	-	ns

#### Notes

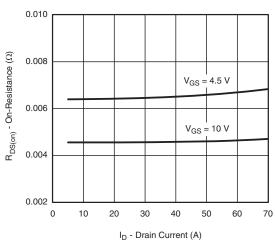
- a. Pulse test: pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

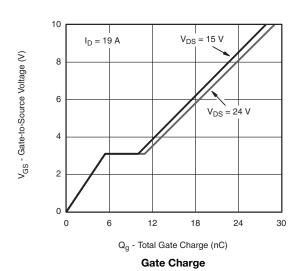


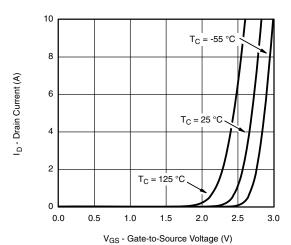


#### **Output Characteristics**

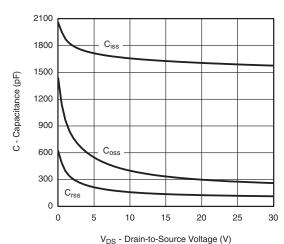


#### On-Resistance vs. Drain Current and Gate Voltage

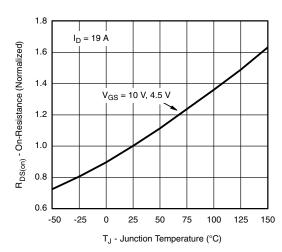




#### **Transfer Characteristics**

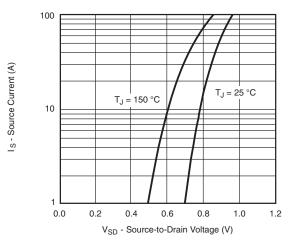


Capacitance

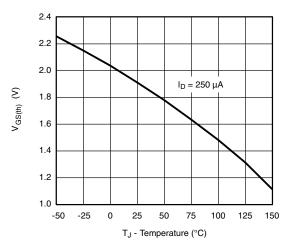


On-Resistance vs. Junction Temperature

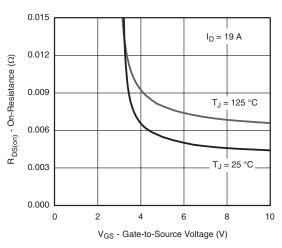




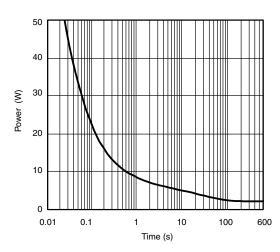
#### Source-Drain Diode Forward Voltage



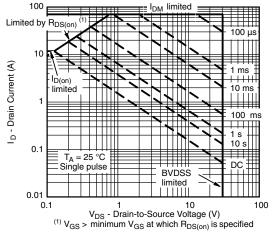
**Threshold Voltage** 



On-Resistance vs. Gate-to-Source Voltage

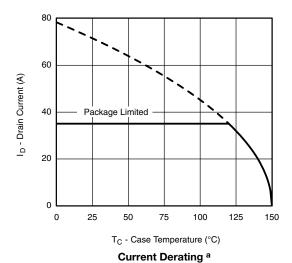


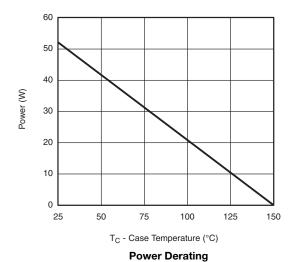
Single Pulse Power (Junction-to-Ambient)



Safe Operating Area, Junction-to-Ambient

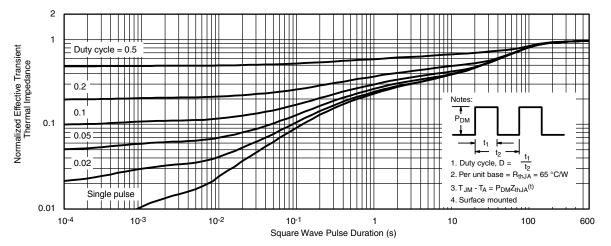




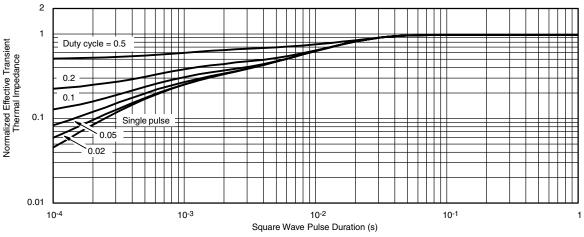


a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



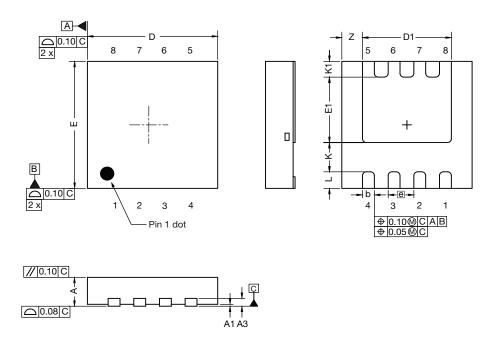
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?75897">www.vishay.com/ppg?75897</a>.



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# Case Outline for PowerPAK® 1212-SWLH and PowerPAK® 1212-8SH



DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	MIN. NOM.	MAX.	
Α	0.82	0.90	0.98	0.032	0.035	0.038	
A1	0.00	-	0.05	0.000	-	0.002	
A3	0.20 ref.			0.008 ref.			
b	0.25	0.30	0.35	0.010	0.012	0.014	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.15	2.25	2.35	0.085	0.089	0.093	
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	1.60	1.70	1.80	0.063	0.067	0.071	
е	0.65 bsc.			0.026 bsc.			
K	0.76 ref.			0.030 ref.			
K1	0.41 ref.			0.016 ref.			
L	0.33	0.43	0.53	0.013	0.017	0.021	
Z	0.525 ref.			0.021 ref.			

DWG: 6062



#### RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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